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Silicon NPN Power Transistors 2SC3148

DESCRIPTION

- With TO-220C package
- High collector breakdown voltage:
  V_{CEO}=800V(Min)
- Excellent switching time:
  t_r=1.0 μ s(Max.)
  t_f=1.0 μ s(Max.@I_C=0.8A

APPLICATIONS

- Switching regulator and high voltage switching applications
- High speed DC-DC converter applications

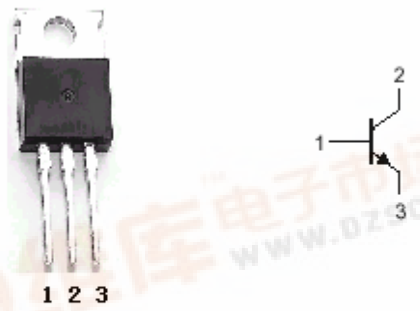

Fig.1 simplified outline (TO-220C) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

固电半导体 INCHANGE SEMICONDUCTOR

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		5	A
I_B	Base current		1	A
P_C	Collector dissipation	T_a=25℃	1.5	W
		T_C=25℃	40	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ; I_B=0	800			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ; I_E=0	900			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=0.8A; I_B=0.16A			0.6	V
V_{BEsat}	Base-emitter saturation voltage	I_C=0.8A; I_B=0.16A			1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=800V ;I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			1	mA
h_{FE}	DC current gain	I_C=0.8A ; V_{CE}=5V	10			
Switching times						
t_r	Rise time	V_{CC}≈400V; I_C=0.8A I_{B1}=0.08A;I_{B2}=-0.20A; R_L=50Ω;Duty cycle≤1%			1.0	μs
t_{stg}	Storage time				4.0	μs
t_f	Fall time				1.0	μs

固电半导体
INCHANGE SEMICONDUCTOR

PACKAGE OUTLINE

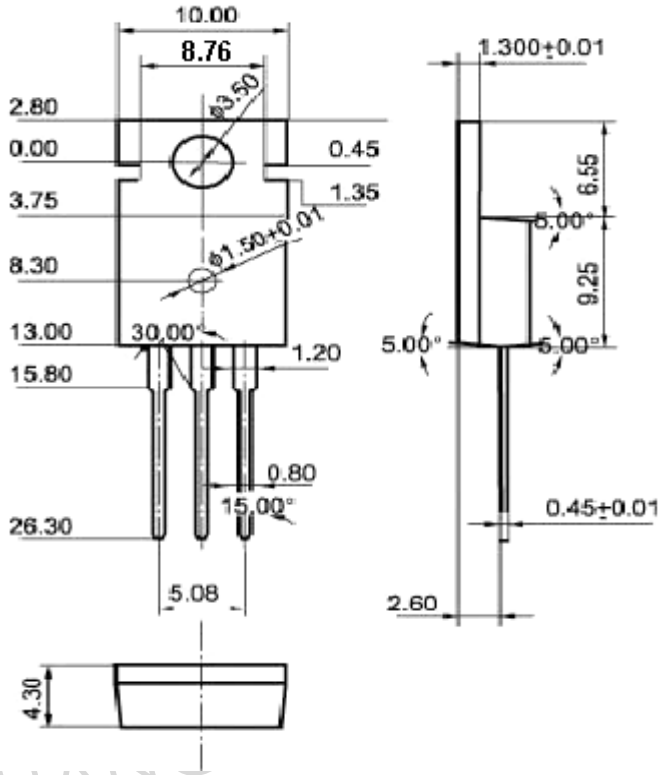

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

固电 UCTOR INCHANGE

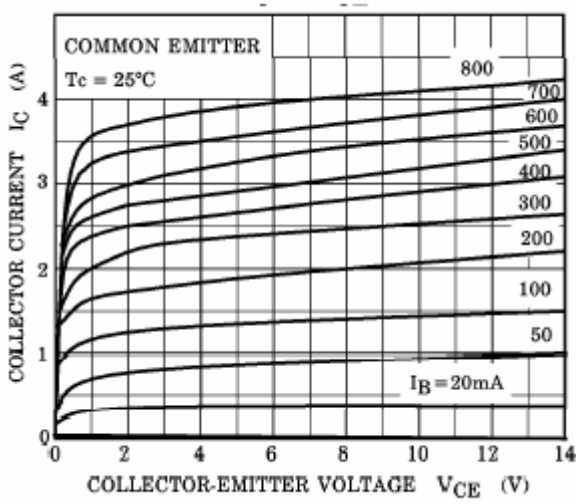

Fig.3 Static Characteristic

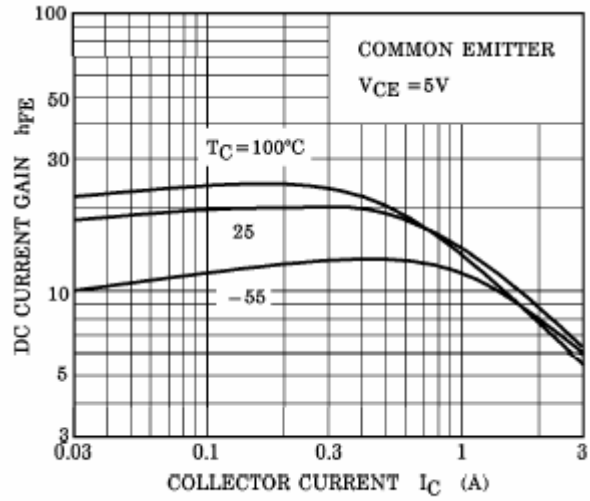

Fig.4 DC current Gain

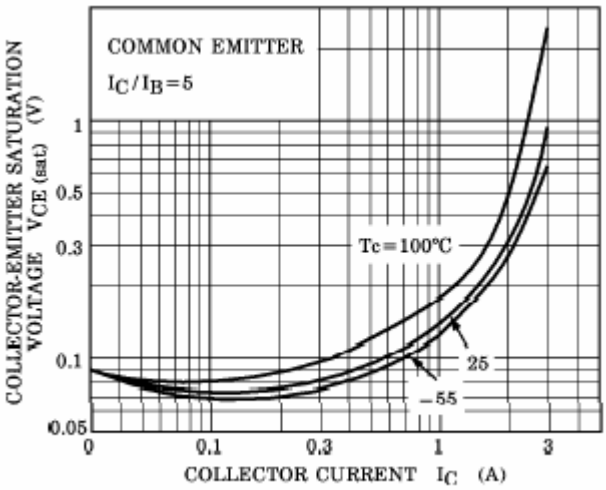

Fig.5 Collector-Emitter Saturation Voltage

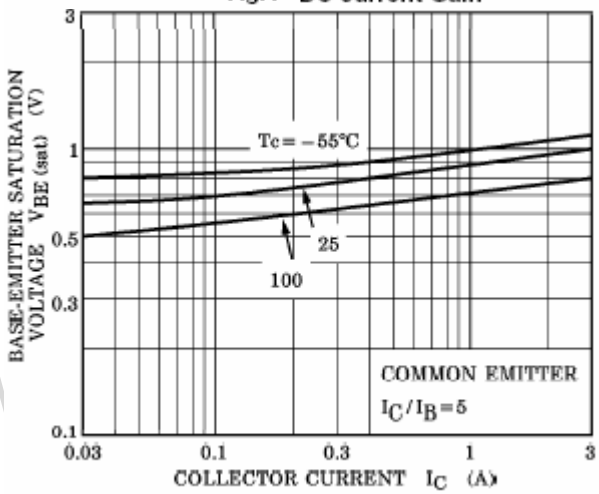

Fig.6 Base-Emitter Saturation Voltage

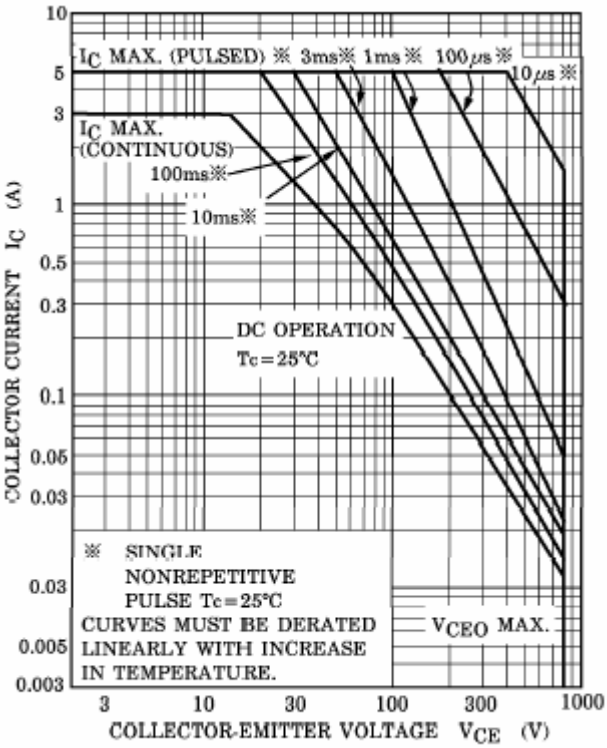

Fig.7 Safe Operating Area